## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: HAYASHI, et al.

Group Art Unit: 2813

Serial No.: 09/955,600

Examiner: NGUYEN, Tuan H.

Niled: September 19, 2001

Confirmation No.: 1668

SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING THE SAME ND METHOD OF FORMING NITRIDE BASED SEMICONDUCTOR LAYER

## PETITION FOR EXTENSION OF TIME

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Date: December 30, 2003

Sir:

Applicants petition the Commissioner for Patents to extend the time for response to the Office Action dated August 1, 2003 for two months from November 1, 2003 to January 1, 2004.

Attached please find a check in the amount of \$420.00 to cover the cost of the extension. In the event that any additional fees are due in connection with this paper, please charge our Deposit Account No. 50-2866. This paper is filed in triplicate.

Respectfully submitted,

WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP

Attorney for Applicants

Reg. No. 32,878

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